CLAIMS:

1. A method used in forming a memory array comprising strings of memory cells, comprising:

forming a stack comprising vertically-alternating first tiers and second tiers;

forming horizontally-elongated trenches into the stack to form laterally-spaced memory-block regions;

forming a wall in individual of the trenches laterally-between immediately ~~-~~laterally ~~-~~adjacent of the laterally-spaced memory-block regions, the forming of the wall comprising:

lining sides of trenches with insulative material comprising at least one ~~of an~~ insulative nitride and elemental-form boron; and

forming a core material in the trenches to span laterally-between the ~~at least one of the insulative nitride and the elemental-form boron~~insulative material.

2. The method of claim 1 wherein the insulative material comprises ~~an insulative~~ one of more members of the group consisting of silicon nitride, boron nitride, carbon nitride, silicon nitride carbide, and germanium nitride.

3. The method of claim 1 wherein the insulative material ~~comprises elemental-form boron~~is devoid of oxygen.

~~4. The method of claim 1 wherein the insulative material comprises both of an insulative nitride and elemental-form boron.~~

~~5. The method of claim 1 comprising forming the individual trenches to have an uppermost minimum lateral width in a vertical cross-section, the insulative material on each side of the core material having a lateral width of 1% to 20% of the uppermost minimum lateral width in the vertical cross-section.~~

~~6~~4. The method of claim 1 comprising:

before forming the wall in the individual trenches, isotropically etching away and replacing sacrificial material that is in the ~~conductive~~ first tiers with conducting material of individual conductive lines;

forming individual memory cells of the strings of memory cells to comprise channel material of channel-material strings in the memory-block regions, a gate region that is part of one of the individual conductive lines in individual of the ~~conductive~~ first tiers, and a memory structure laterally-between the gate region and the channel material of the channel-material strings in the individual ~~conductive~~ first tiers, forming the channel-material strings before forming the conducting material of the individual conductive lines; and

after the replacing, forming the wall in the individual trenches.

~~7~~5. A method used in forming a memory array comprising strings of memory cells, comprising:

forming a stack comprising vertically-alternating first tiers and second tiers;

forming horizontally-elongated trenches into the stack to form laterally-spaced memory-block regions;

~~through the trenches, isotropically etching away and replacing sacrificial material that is in the conductive tiers with conducting material of individual conductive lines;~~

~~forming individual memory cells of the strings of memory cells to comprise channel material of channel-material strings in the memory-block regions, a gate region that is part of one of the individual conductive lines in individual of the conductive tiers, and a memory structure laterally-between the gate region and the channel material of the channel-material strings in the individual conductive tiers, forming the channel-material strings before forming the conducting material of the individual conductive lines;~~

~~after the replacing,~~ forming a wall in individual of the trenches ~~laterally~~ between immediately ~~laterally~~ adjacent of the laterally-spaced memory-block regions, the forming of the wall comprising:

lining sides of trenches with insulative material comprising ~~at least one of~~ an insulative nitride and optionally elemental-form boron ~~that is directly against the conducting material of the individual conductive lines~~; and

forming a core material in the trenches ~~spanning~~ to span laterally between the ~~at least one of the~~ insulative ~~nitride~~material, the individual trenches having an uppermost minimum lateral width in a vertical cross-section, ~~and the elemental-form boron, the forming of the core material comprising:~~

~~forming a laterally-outer silicon dioxide that is directly against said at least one of insulative nitride and elemental-form boron; and~~

~~forming polysilicon directly against and to span laterally between said laterally-outer silicon dioxide~~the insulative material on each side of the core material having a lateral width of 1% to 20% of the uppermost minimum lateral width in the vertical cross-section.

~~8~~6. A method used in forming a memory array comprising strings of memory cells, comprising:

~~a vertical~~forming a stack comprising vertically-alternating ~~insulative~~ first tiers and ~~conductive~~ second tiers~~;, the conductive tiers individually comprising conductive lines;~~

forming horizontally-elongated trenches into the stack to form laterally-spaced memory-block regions;

through the trenches, isotropically etching away and replacing sacrificial material that is in the first tiers with conducting material of individual conductive lines;

forming individual memory cells of the strings of memory cells ~~in the stack comprising channel material extending through the insulative tiers and the conductive tiers; individual of the memory cells comprising~~to comprise ~~the~~ channel material of channel-material strings in the memory-block regions, a gate region that is part of one of the individual conductive lines in individual of the ~~conductive~~ first tiers, and a memory structure laterally-between the gate region and the channel material of the channel-material strings in the individual first tiers, forming the channel-material strings before forming the conducting material of the ~~in the~~ individual conductive ~~tiers~~lines; ~~and~~

after the replacing, forming a wall~~s~~ in individual~~ly~~ of the trenches laterally-between immediately adjacent of the laterally-spaced memory-block regions, the forming of the wall comprising;

lining sides of the trenches with ~~extending through the insulative tiers and the conductive tiers laterally between immediately adjacent of the conductive lines, the walls individually comprising laterally-outer insulative material and a core material spanning laterally-between the laterally-outer insulative material, the laterally-outer~~ insulative material comprising at least one ~~of an~~ insulative nitride and elemental-form boron that is directly against the conducting material of the individual conductive lines; and

forming a core material in the trenches spanning laterally between the insulative material, the forming of the core material comprising:

forming a laterally-outer silicon dioxide that is directly against said at least one of insulative nitride and elemental-form boron; and

forming polysilicon directly against and to span laterally-between said laterally-outer silicon dioxide.

~~9. The memory array of claim 8 wherein the laterally-outer insulative material comprises an insulative nitride.~~

~~10. The memory array of claim 9 wherein the insulative nitride comprises one or more of boron nitride, carbon nitride, silicon nitride, silicon nitride carbide, and germanium nitride.~~

~~11. The memory array of claim 8 wherein the laterally-outer insulative material comprises elemental-form boron.~~

~~12. The memory array of claim 8 wherein the laterally outer insulative material comprises both insulative nitride and elemental form boron.~~

~~13. The memory array of claim 8 wherein the laterally outer insulative material is devoid of oxygen.~~

~~14. The memory array of claim 8 wherein the at least one of insulative nitride and elemental form boron is directly against conducting material of the conductive lines.~~

~~15. The memory array of claim 8 wherein the core material at least predominately comprises insulative material.~~

~~16. The memory array of claim 8 wherein the core material at least predominately comprises conductive material.~~

~~17. The memory array of claim 8 wherein the core material at least predominately comprises semiconductive material.~~

~~18. The memory array of claim 17 wherein the semiconductive material at least predominately comprises undoped elemental form silicon.~~

~~19. The memory array of claim 8 wherein, in a vertical cross-section, the laterally outer insulative material on each side of the core material has a lateral width of 1% to 20% of an uppermost minimum lateral width of the individual wall in the vertical cross-section.~~

~~20. The memory array of claim 8 wherein the core material is homogenous.~~

~~21. The memory array of claim 8 wherein the core material is not homogenous.~~

~~22. The memory array of claim 21 wherein the core material comprises a laterally outer insulative oxide and a laterally inner material that is not an insulative oxide.~~

~~23. The memory array of claim 22 wherein the laterally outer insulative material comprises silicon nitride.~~

~~24. The memory array of claim 21 comprising void space in the core material.~~

~~25. The memory array of claim 8 comprising NAND.~~

~~26. A memory array comprising strings of memory cells, comprising:~~

~~a vertical stack comprising alternating insulative tiers and conductive tiers, the conductive tiers individually comprising conductive lines comprising conducting material;~~

~~strings of memory cells in the stack comprising channel material extending through the insulative tiers and the conductive tiers; individual of the memory cells comprising the channel material, a gate region that is part of one of the conductive lines in individual of the conductive tiers, and a memory structure laterally between the gate region and the channel material in the individual conductive tiers; and~~

~~walls individually extending through the insulative tiers and the conductive tiers laterally between two of the conductive lines, the walls individually comprising laterally outer insulative material and a core material spanning laterally between the laterally outer insulative material, the laterally outer insulative material comprising at least one of an insulative nitride and elemental form boron that is directly against the conducting material of the conductive lines, the core material comprising:~~

~~a laterally outer silicon dioxide that is directly against said at least one of insulative nitride and elemental form boron; and~~

~~polysilicon directly against and spanning laterally between said laterally outer silicon dioxide.~~